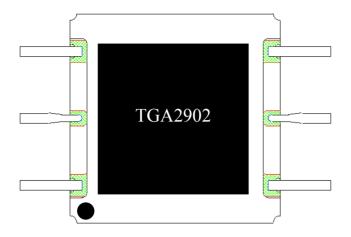


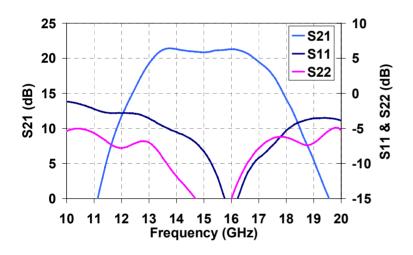
13 - 15 GHz 2 Watt Packaged Amplifier

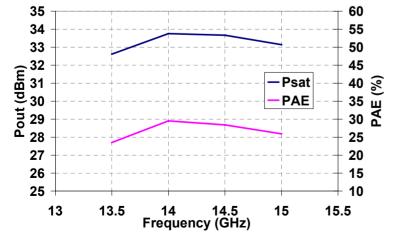
TGA2902-EPU



Preliminary Measured Performance

Bias Conditions: Vd=7V Id=640mA





Key Features and Performance

- 33.5 dBm Midband Pout
- 22 dB Nominal Gain
- 8 dB Typical Input Return Loss
- 10 dB Typical Output Return Loss
- Directional Power Detector with Reference
- 0.5µm pHEMT Technology
- Bias Conditions: 7V, 640mA
- Chip dimensions: 2.0 x 1.4 x 0.1 mm (80 x 55 x 4 mils)

Primary Applications

- VSAT
- Point to Point



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TABLE I MAXIMUM RATINGS

Symbol	Parameter <u>4</u> /	Value	Notes
V ⁺	Positive Supply Voltage	8 V	<u>3</u> /
V	Negative Supply Voltage Range	-5V to 0V	
I ⁺	Positive Supply Current (Quiescent)	TBD	<u>3</u> /
I _G	Gate Supply Current	18 mA	
P _{IN}	Input Continuous Wave Power	24 dBm	<u>3</u> /
P_{D}	Power Dissipation	TBD	<u>3</u> /
T _{CH}	Operating Channel Temperature	150 ⁰ C	<u>1</u> / <u>2</u> /
T _M	Mounting Temperature (30 Seconds)	320 °C	
T _{STG}	Storage Temperature	-65 to 150 °C	

- 1/ These ratings apply to each individual FET.
- $\underline{2}$ / Junction operating temperature will directly affect the device median time to failure (T_M). For maximum life, it is recommended that junction temperatures be maintained at the lowest possible levels.
- $\underline{3}/$ Combinations of supply voltage, supply current, input power, and output power shall not exceed P_D .
- 4/ These ratings represent the maximum operable values for this device.





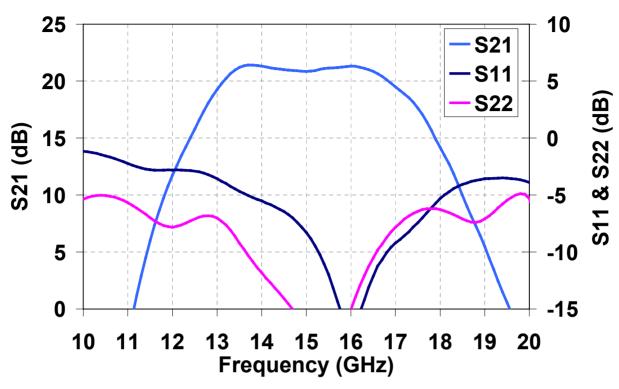
TABLE II RF CHARACTERIZATION TABLE ($T_A = 25$ °C, Nominal) (Vd = 7V, Id = 640mA ± 5 %)

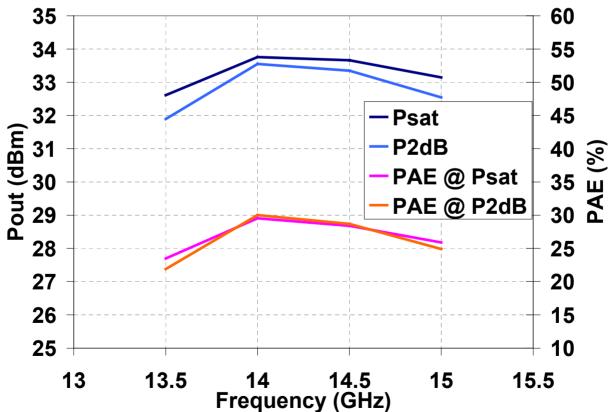
SYMBOL	PARAMETER	TEST	LIMITS			UNITS
		CONDITION	MIN	TYP	MAX	
Gain	Small Signal Gain	F = 13.75-14.5		22		dB
IRL	Input Return Loss	F = 13.75-14.5		8		dB
ORL	Output Return Loss	F = 13.75-14.5		10		dB
PWR	Output Power @ P2dB	F = 13.75-14.5		33.5		dBm
PAE	Power Added Efficiency @ P2dB	F = 13.75-14.5		27		%

Note: Table III Lists the RF Characteristics of typical devices as determined by fixtured measurements.



Typical Performance



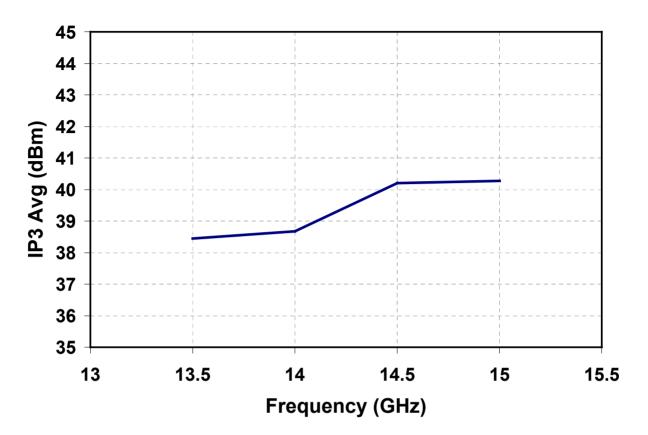




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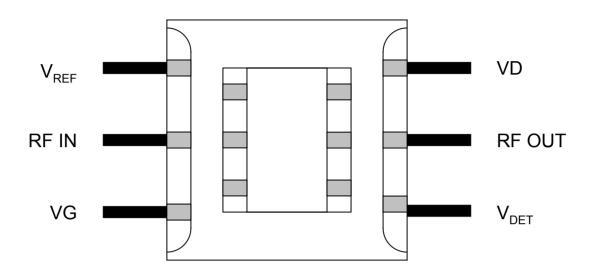
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Typical Performance





Package Pinout Diagram

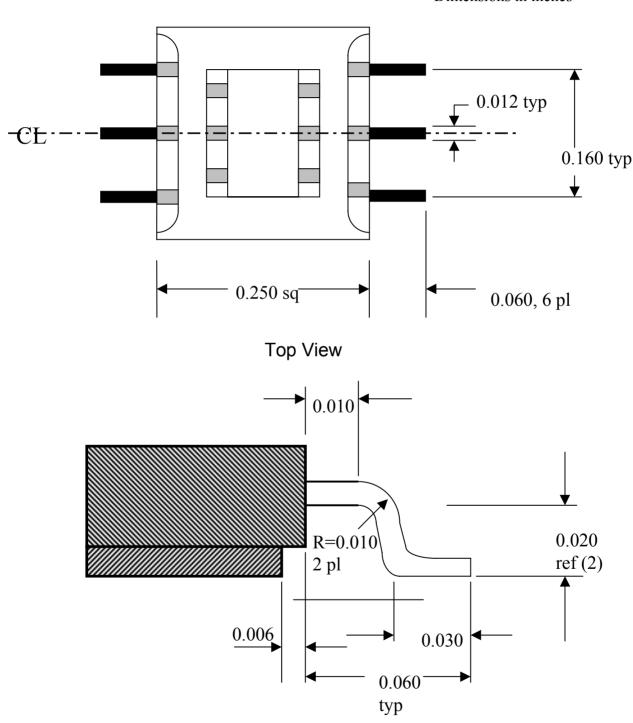


GaAs MMIC devices are susceptible to damage from Electrostatic Discharge. Proper precautions should be observed during handling, assembly and test.



Mechanical Drawing

Dimensions in inches

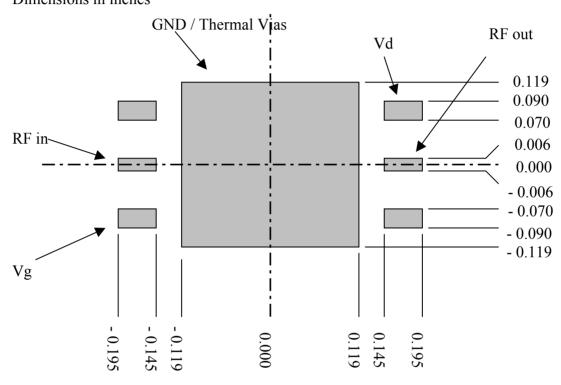


Side View



Recommended PWB Land Pattern

Dimensions in inches

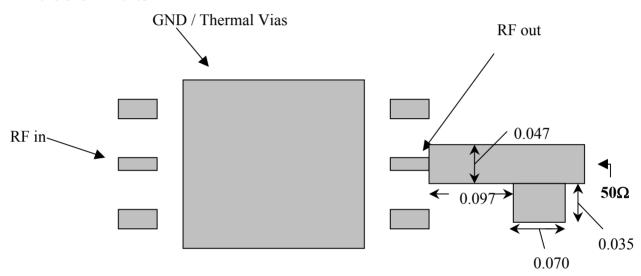




Required Tuning Stub

Shown on Rogers RO4003_® high frequency laminates 0.020" board $(\varepsilon_r = 3.38)$

Dimensions in inches



RO4003 @is a registered trademark of Rogers Corporation.



0.6

0.5

0.4

0.3

0.2

0.1

0

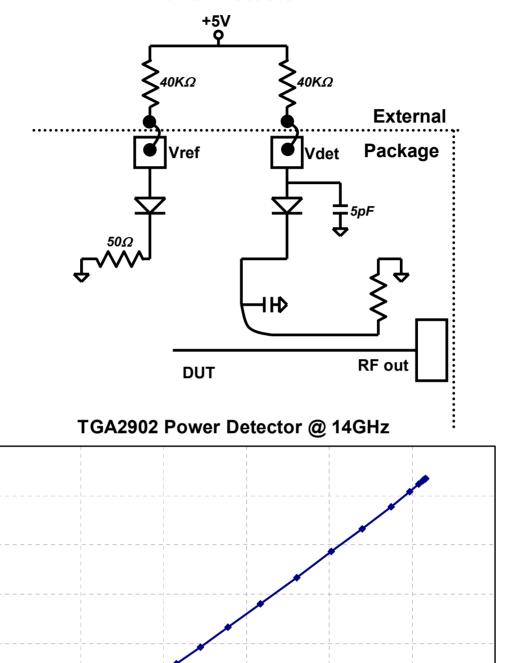
0

10 (20 dBm)

Vref-Vdet (V)

TGA2902-EPU

Power Detector



Note: Devices designated as EPU are typically early in their characterization process prior to finalizing all electrical and process specifications. Specifications are subject to change without notice.

20 (26 dBm) 60

50 (34 dBm)

sqrt Pout (mW^0.5)

30 40 (29.5 dBm) (32 dBm)